

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A III-V group nitride system semiconductor substrate, comprising:

III-V group nitride system single crystal;

wherein said III-V group nitride system semiconductor substrate has a flat surface and satisfies the relationship of $\theta > \alpha$, where θ [deg] is given as an average in angles of the substrate surface to low index surfaces closest to the substrate surface measured at a plurality of arbitrary points in plane of the substrate, and α [deg] represents a difference of θ and an inclination value measured at a point farthest from θ . a variation range of said measured angles to θ is represented by $\pm \alpha$ [deg].

Claims 2-3 (Canceled).

4. (Currently Amended) ~~[[A]] The~~ III-V group nitride system semiconductor substrate according to claim 1, wherein; ~~comprising;~~

~~III-V group nitride system single crystal;~~

~~wherein said III-V group nitride system semiconductor substrate has a flat surface and satisfies the relationship of $\theta > \alpha$, where θ [deg] is given as an average in angles of the substrate surface to low index surfaces closest to the substrate surface measured at a plurality of arbitrary points in plane of the substrate, and a variation range of said measured angles to θ is represented by $\pm \alpha$ [deg], and the inclination direction at an arbitrary point in plane of the substrate is nearly constant.~~

5. (Currently Amended) ~~[[A]] The~~ III-V group nitride system semiconductor substrate according to claim 1, wherein; ~~comprising;~~

~~III-V group nitride system single crystal;~~

~~wherein said III-V group nitride system semiconductor substrate has a flat surface and satisfies the relationship of $\theta > \alpha$, where θ [deg] is given as an average in angles of the substrate surface to low index surfaces closest to the substrate surface measured at a plurality of arbitrary points in plane of the substrate, and a variation range of said measured angles to θ is represented by $\pm \alpha$ [deg], and the direction distribution range of vector projected onto the substrate surface of the normal vector of low index surfaces closest to the substrate surface at a plurality of arbitrary points in plane of the substrate is less than 180 [deg].~~

6. (Original) The III-V group nitride system semiconductor substrate according to claim 1, wherein:

said III-V group nitride system single crystal is hetero-epitaxially grown on a hetero-substrate.

7. (Original) The III-V group nitride system semiconductor substrate according to claim 1, wherein:

said III-V group nitride system single crystal composes a self-standing substrate.

8. (Currently Amended) The III-V group nitride system semiconductor substrate according to claim 1, wherein:

said III-V group nitride system single crystal is of a hexagonal system.

9. (Currently Amended) The III-V group nitride system semiconductor substrate according to claim 1, wherein:

said III-V group nitride system single crystal is of a hexagonal system and said low index surface closest to the substrate surface is C-face.

10. (Currently Amended) The III-V group nitride system semiconductor substrate according to claim 1, wherein:

said III-V group nitride system single crystal is of a hexagonal system and said low index surface closest to the substrate surface is A-face, M-face or R-face.

11. (Original) The III-V group nitride system semiconductor substrate according to claim 1, wherein:

said substrate surface is mirror-finished by polishing.

12. (Original) The III-V group nitride system semiconductor substrate according to claim 1, wherein:

said θ is 10 or less [deg].

13. (Original) The III-V group nitride system semiconductor substrate according to claim 1, wherein:

said α is 1.0 or less [deg].

14. (Original) The III-V group nitride system semiconductor substrate according to claim 1, wherein:

said θ is 10 or less [deg] and said α is 1.0 or less [deg].

15. (Original) The III-V group nitride system semiconductor substrate according to claim 1; wherein:

said low index surfaces closest to the substrate surface are C-face and the inclination direction of said low index surfaces to the substrate surface is in A-axis direction.

16. (Original) The III-V group nitride system semiconductor substrate according to claim 1, wherein:

said low index surfaces closest to the substrate surface are C-face and the inclination direction of said low index surfaces to the substrate surface is in M-axis direction.